

Yuichi Fujita

List of Publications by Year in descending order

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papers

561
citations

623734

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docs citations

36
times ranked

331
citing authors

#	ARTICLE	IF	CITATIONS
1	Fabrication of Co ₂ FeSi Heusler-alloy epitaxial film on NbN epilayer with improved surface morphology. Thin Solid Films, 2022, 745, 139084.	1.8	3
2	Spin-scattering asymmetry at half-metallic-ferromagnet ferromagnet interface. Physical Review B, 2021, 104, .	3.2	1
3	Superimposed contributions to two-terminal and nonlocal spin signals in lateral spin-transport devices. Physical Review B, 2021, 104, .	3.2	3
4	Effects of the atomic order on the half-metallic electronic structure in the C_{122}		

#	ARTICLE	IF	CITATIONS
19	Spin Transport and Relaxation up to 250K in Heavily Doped n -Type Ge Detected Using Co Physical Review Applied, 2017, 8, .	3.8	52
20	Large impact of impurity concentration on spin transport in degenerate n -Ge. Physical Review B, 2017, 95, .	3.2	22
21	Control of electrical properties in Heusler-alloy/Ge Schottky tunnel contacts by using phosphorous $\hat{\Gamma}$ -doping with Si-layer insertion. Materials Science in Semiconductor Processing, 2017, 70, 83-85.	4.0	12
22	Giant Spin Accumulation in Silicon Nonlocal Spin-Transport Devices. Physical Review Applied, 2017, 8, .	3.8	47
23	Spin signals in Si non-local transport devices with giant spin accumulation. , 2017, , .		1
24	Finely Controlled Approaches to Formation of Heusler-Alloy/Semiconductor Heterostructures for Spintronics. Materials Transactions, 2016, 57, 760-766.	1.2	14
25	Temperature-independent spin relaxation in heavily doped n -type germanium. Physical Review B, 2016, 94, .	3.2	30
26	A low-temperature fabricated gate-stack structure for Ge-based MOSFET with ferromagnetic epitaxial Heusler-alloy/Ge electrodes. Japanese Journal of Applied Physics, 2016, 55, 063001.	1.5	3
27	Effect of Sn-doped Ge insertion layers on epitaxial growth of ferromagnetic Fe_3Si films on a flexible substrate. , 2014, , .		0
28	A magnetic tunnel junction with an L21-ordered Co_2FeSi electrode formed by all room-temperature fabrication processes. Thin Solid Films, 2014, 557, 386-389.	1.8	7
29	Greatly enhanced generation efficiency of pure spin currents in Ge using Heusler compound Co_2FeSi electrodes. Applied Physics Express, 2014, 7, 033002.	2.4	65
30	Room-temperature sign reversed spin accumulation signals in silicon-based devices using an atomically smooth $\text{Fe}_3\text{Si}/\text{Si}(111)$ contact. Journal of Applied Physics, 2013, 113, .	2.5	14
31	Room-temperature detection of spin accumulation in silicon across Schottky tunnel barriers using a metal-oxide-semiconductor field effect transistor structure (invited). Journal of Applied Physics, 2013, 113, .	2.5	20
32	(Invited) SiGe Spintronics with Single-Crystalline Ferromagnetic Schottky-Tunnel Contacts. ECS Transactions, 2013, 50, 235-243.	0.5	0
33	Room-Temperature Tunneling Magnetoresistance in Magnetic Tunnel Junctions with a $\text{D}_{03}\text{-Fe}_3\text{Si}$ Electrode. Japanese Journal of Applied Physics, 2013, 52, 04CM02.	1.5	10
34	Crystal Growth in Laser Surface Melting and Cladding of Ni-Base Single Crystal Superalloy. Welding in the World, Le Soudage Dans Le Monde, 2008, 52, 64-78.	2.5	17
35	Crystalline controlled build-up repairing utilizing unidirectional solidification. Welding International, 2007, 21, 782-789.	0.7	0
36	Detection of flaws in ferromagnetic samples based on low frequency eddy current imaging. Journal of Applied Physics, 2003, 93, 8277-8279.	2.5	7